

ABSTRACT

Disclosed is a method of manufacturing a semiconductor device. In this method, a concave portion (7) is formed in one surface in the thickness direction of a primary base plate (1) comprising a semiconductor substrate with a relatively large thickness dimension. Then, through-holes (4a, 4b) are formed by a reactive-ion etching process using as a mask an opening (8) formed in an oxide film (6a) provided on the other surface in the thickness direction of the primary base plate (1). The opening (8) has a narrow width in a region corresponding to the concave portion (7) and a wide width in the remaining region. Thus, respective times necessary for the wide-width through-hole (4a) to penetrate through the primary base plate (1) and necessary for the narrow-width through-hole (4b) to reach a bottom surface of the concave portion (7) can be approximately equalized to complete the common etching process of the wide-width through-hole (4a) and the narrow-width through-hole (4b) approximately simultaneously.